# Elec

### Imaging at the Nanoscale -Electron and X-Ray Beams

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Nanoparticles



#### New Materials



#### Integrated Circuits





## Similar challenges (and tools) for semiconductor and life sciences

#### T2 Bacteriophage



2007



Single atom P. Voyles, D. Muller, J. Grazul, P. Citrin, H. Gossmann, *Nature* 416 826 (2002)
Sensitivity: U. Kaiser, D. Muller, J. Grazul, M. Kawasaki, *Nature Materials*, 1 102 (2002)

### Why is the Probe so Large?

- Probe diameter is ~ 2 Å
- Electron Wavelength at 200 kV is 0.0251 Å
- Non-ideal lenses in large aberrations in tiny numerical apertures



Corrector Benefits: Increased current, resolution, contrast [see P. E. Batson *et al.*, *Nature* **418**, 617 (2002)]



contrast or current.

### Aberration-Corrected STEM







NION SuperSTEM with PEELS

- 0.4 eV energy resolution
- 0.05 nm spatial resolution
- 1 nm depth of focus -> 3D!
- EELS spectral maps in real time

This will be the world's first 5<sup>th</sup>-order corrected STEM (x 4 improvement over previous)





Single atom P. Voyles, D. Muller, J. Grazul, P. Citrin, H. Gossmann, *Nature* 416 826 (2002)
Sensitivity: U. Kaiser, D. Muller, J. Grazul, M. Kawasaki, *Nature Materials*, 1 102 (2002)

#### 3D-Characterization of Si Nanoparticles embedded in Silicon Oxide





Tomographic reconstruction of the Silicon plasmon signal at 17eV

### Silicon Nano-particles Embedded in Silicon Oxide







Tomographic reconstruction of the Silicon plasmon signal at 17eV



D. A. Muller et al., Nature **399**, 758 (1999).



Theory in

J. B. Neaton, D. A. Muller, and N. W. Ashcroft, Phys. Rev. Lett. 85, 1298 (2000).





### How Bad is Radiation Damage?

R. Henderson, Quarterly Reviews of Biophysics 28 (1995) 171-193.





It's not the cross-section, but

How many damaging events per useful imaging event?

Least Damage: Elastic imaging - Electrons wins Inelastic imaging - Soft X-rays win



Data from Breedlove and Trammell, Science 170 (1970) 1310-1313

For electrons  $\sigma_i / \sigma_e \sim ln (E)$ 

#### What Causes the Damage?

(Temperature rise is < 2K- smaller beam is less)



coronene (Stevens, 2000)

- -× · PE (Boudet and Roucau, 1985)
- behenic acid (Ohno, 2000)
- DCHD (Liao and Martin, 1993)
- PE (Kumar and Adams, 1990)
- -E-DCHD (Read and Young, 1985)
  - PE LVEM (Martin and Drummy, 2001) +
- Pentacene (Drummy, 2002)
- p-terphenyl (Howie, 1985)



Calculated C-K shell ionization **Cross-section** 

Suggests Auger Transitions could be suspect, Rather than the 20 eV valence losses

LF Drummy et al. Ultramicroscopy 99 247-256

#### Electron Beam (400 keV) Radiation Damage in Vitreous Ice



(Damage Threshold ~ 500 e<sup>-</sup>/nm<sup>2</sup>)











It's almost impossible to do atomic-resolution phase contrast imaging with biological samples (except by averaging over many similar molecules)!



B. F. McEwen et al, Journal of Structural Biology **138** 47–57 (2002) Saxberg & Saxton, W.O., Ultramicroscopy **6**, 85–90 (1981)



Small features have low contrast (and for a fixed dose we trade 2D resolution for contrast)

Resolution  $\alpha$  Sample Thickness



Need to make thin samples (true for x-rays as well as electrons)

(unless we have a fluorescence detection method)

### Focused Ion Beam Milling

#### Cut out a shape with a 5-30 keV Ga+ ion beam



Pick up of TEM lemella with Lift-out Tool



Sample can be As thin as 100 nm (but damage layer Is 10-30 nm/side)

Hitachi Review Vol. 54 (2005), No. 1 29



Fig. 4—Observation Examples of DRAM Capacitor Plug (2-µm square).



Water Droplets in Liquid Margarine

### Tomography at the Nanoscale







Walter Hoppe, Angew. Chem. Int. Ed. Engl. 22 (1983) 456-485

#### **3D resolution function**

along X,  $dx \sim 0.2$  nm along Y, dy  $\sim 1$  nm along Z,  $dz \sim 1$  nm (due to limited tilt range and finite number of projection images)

Sample thickness: 20-600 nm



### High tilt tomography holder (Fischione 2020)







No tilt (0°)



-80°

Low magnification (57x) CCD image





Limit of goniometer  $\alpha$  tilt



### Finite Sampling





• Matthew Weyland

#### **Determining the tilt axis**





Single Image



Projection through aligned series





Power spectrum of (b)

**Matthew Weyland** 

### Stress Void Reconstruction









Via is 250 nm thick, inside a 500 nm thick Cu section

P. Ercius, M. Weyland, D. A. Muller, L. M. Gignac, Appl. Phys. Lett. 88 243116 (2006).







### Environmental Sensitivity



We don't just see atoms:

•Can detect moving chairs, elevators, trucks and air pressure changes.

•"Drift to the right, rain tonight"





### Radiant Cooling Panels: Heat Transfer without Airflow



(allows us to cut back airflow – which is now used to control humidity)



- •Radiant cooling panel temperature regulated by closed-loop chiller
- •Brings room into thermal equilibrium with panels by radiative transfer
- •By tuning the panel temperature, we can keep the building heat from pulsing
- •Effect is to add a huge thermal mass to the room (a giant wine cellar)





## Outlook



• Electron Microscopy: 0.5-0.7 Å resolution (1-2 Å standard today) 0.1-0.5 eV energy resolution Sample thickness < 100-1000 nm Small working distance (~3-10 mm) Nitride-window e-cells for imaging liquids

• X-Ray Microscopy:

Radiation damage will be worse for elastic imaging (1/r<sup>4</sup> in 3D)
Best resolution will require TEM-like sample preparation

+10 nm res & 1- 10  $\mu m$  thick samples for whole-cell mapping







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Imaging Individual Dopant Atoms (Bell Labs)

• Paul Voyles, John Grazul, Hans Gossmann, Paul Citrin, Ute Kaiser (*Jena*)

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### Electron Backscatter Imaging





EBSD, EMPA, John Hunt hunt@ccmr.cornell.edu



Use electron channeling patterns to Produce maps of grain orientations



Needs clean surfaces, grains > 200 nm

(With a FEG-SEM, as small as 20-50 nm)